

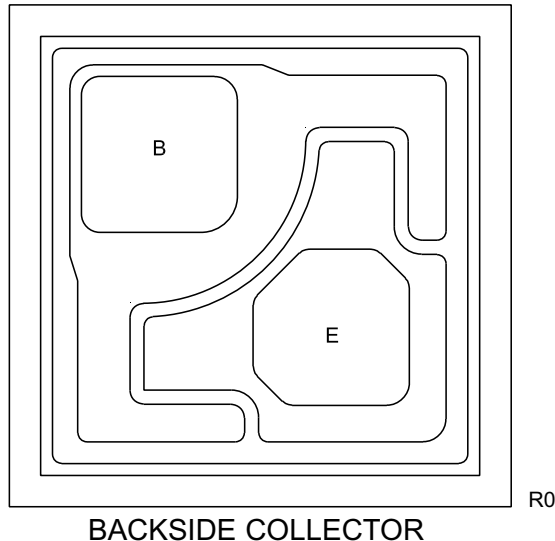
PROCESS CP392V
Smal Signal Transistor
NPN - Amp/Switch Transistor Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.7 x 3.7 MILS
Emitter Bonding Pad Area	3.7 x 3.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR

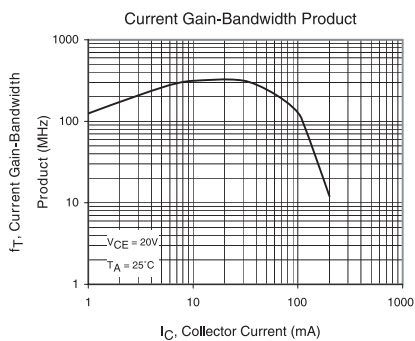
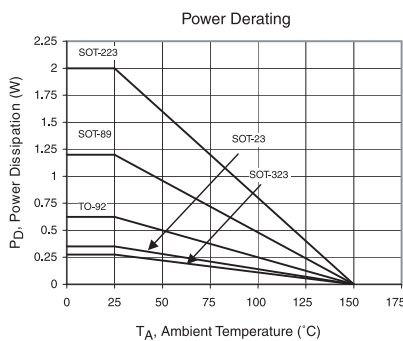
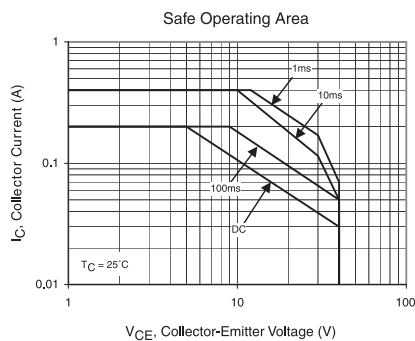
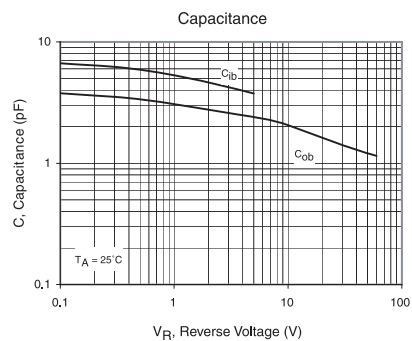
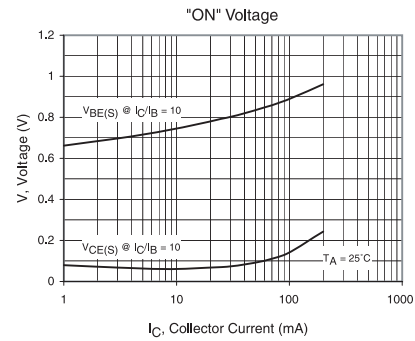
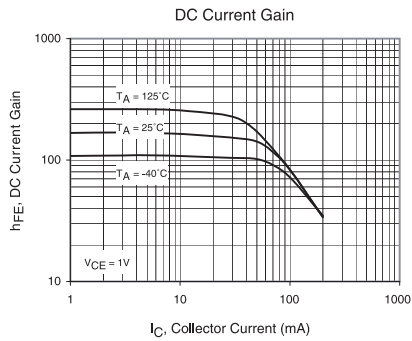
GROSS DIE PER 4 INCH WAFER
93,826

PRINCIPAL DEVICE TYPES

2N3904
CMKT3904
CMLT3904E
CMPT3904
CMPT3904E
CMST3904
CXT3904
CZT3904

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